

AMENDMENTS TO THE SPECIFICATION

Please amend the specification as follows:

Page 12, second full paragraph:

The gate oxide thickness of the high-breakdown-voltage output driver M6 is the same as that of MOS transistors (not shown in FIG. 2) used in the low-breakdown-voltage regulator 12. The gate oxides film of the output driver M6 and the low-breakdown-voltage MOS transistors are thinner than the gate oxides film of high-breakdown-voltage MOS transistors (not shown in FIG. 2) used in the high-breakdown-voltage regulator 11 ~~12~~.